## NLAS4717

## Analog Switch, High Bandwidth, Dual SPDT

The NLAS4717 is an advanced CMOS analog switch fabricated in sub-micron silicon gate CMOS technology. The device is a dual independent Single Pole Double Throw (SPDT) switch featuring two low $\mathrm{R}_{\mathrm{DS}(\text { on) }}$ of $4.5 \Omega$ at 3.0 V .

The device also features guaranteed Break-Before-Make (BBM) switching, assuring the switches never short the driver.

The NLAS4717 is available in two small size packages:

- Micro10
$3.0 \times 5.0 \mathrm{~mm}$
- Flip-Chip-10: $2.0 \times 1.5 \mathrm{~mm}$


## Features

- Low $\mathrm{R}_{\mathrm{DS}(\text { on) }}: 4.5 \Omega$ @ 3.0 V
- Matching Between the Switches $\pm 0.5 \Omega$
- Wide Low Voltage Range: 1.8 V to 5.5 V
- High Bandwidth $>40 \mathrm{MHz}$
- 1.65 V to 5.5 V Operating Range
- Low Threshold Voltages on Pins 4 and 8 (CTRL Pins)
- Ultra-Low Charge Injection $\leq 6.0 \mathrm{pC}$
- Low Standby Current $-\mathrm{I}_{\mathrm{CC}}=1.0 \mathrm{nA}(\operatorname{Max}) @ \mathrm{~T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$
- OVT* on Pins 4 and 8 (CTRL Logic Pins)
- Pb-Free Packages are Available


## Typical Applications

- Cell Phones
- PDAs
- MP3s
- Digital Still Cameras


## Important Information

- ESD Protection:

$$
\mathrm{HBM}=2000 \mathrm{~V}, \mathrm{MM}=200 \mathrm{~V}
$$

- Latchup Max Rating: 200 mA (Per JEDEC EIA/JESD78)
- Pin-to-Pin Compatible with MAX4717


## *OVT

- Overvoltage Tolerance (OVT) specific pins to operate higher than normal supply voltages, with no damage to the devices or to signal integrity.



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## http://onsemi.com

MARKING
DIAGRAMS

## FUNCTION TABLE

| IN_ | NO_ | NC $_{-}$ |
| :---: | :---: | :---: |
| 0 | OFF | ON |
| 1 | ON | OFF |

ORDERING INFORMATION

| Device | Package | Shipping $^{\dagger}$ |
| :---: | :---: | :---: |
| NLAS4717FCT1 | Flip-Chip-10 | $3000 /$ <br> Tape \& Reel |
| NLAS4717FCT1G | Flip-Chip-10 <br> (Pb-Free) | $3000 /$ <br> Tape \& Reel |
| NLAS4717MR2 | Micro10 | $4000 /$ <br> Tape \& Reel |
| NLAS4717MR2G | Micro10 <br> (Pb-Free) | $4000 /$ <br> Tape \& Reel |

$\dagger$ For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.


Figure 1. Device Circuit Diagrams and Pin Configurations

## MAXIMUM RATINGS

| Symbol | Parameter | Value | Unit |
| :---: | :--- | :---: | :---: |
| $\mathrm{V}_{+}$ | Positive DC Supply Voltage | -0.5 to +7.0 | V |
| $\mathrm{~V}_{\mathrm{IS}}$ | Analog Input Voltage ( $\mathrm{V}_{\mathrm{NO}}, \mathrm{V}_{\mathrm{NC}}$, or $\mathrm{V}_{\mathrm{COM}}$ ) (Note 1) | $-0.5 \leq \mathrm{V}_{\mathrm{IS}} \leq \mathrm{V}_{\mathrm{CC}}+0.5$ | V |
| $\mathrm{~V}_{\mathrm{IN}}$ | Digital Select Input Voltage | $-0.5 \leq \mathrm{V}_{\mathrm{I}} \leq+7.0$ | V |
| $\mathrm{I}_{\mathrm{IK}}$ | DC Current, Into or Out of Any Pin (Continuous) | $\pm 100$ | mA |
| $\mathrm{I}_{\mathrm{PK}}$ | Peak Current (10\% Duty Cycle) | $\pm 200$ | mA |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Signal voltage on NC, NO, and COM exceeding VCC or GND are clamped by the internal diodes. Limit forward diode current to maximum current rating.

## RECOMMENDED OPERATING CONDITIONS

| Symbol | Parameter | Min | Max | Unit |
| :---: | :--- | :---: | :---: | :---: |
| $\mathrm{V}_{+}$ | DC Supply Voltage | 1.8 | 5.5 | V |
| $\mathrm{~V}_{\mathrm{IN}}$ | Digital Select Input Voltage | GND | 5.5 | V |
| $\mathrm{~V}_{\text {IS }}$ | Analog Input Voltage (NC, NO, COM) | GND | $\mathrm{V}_{\mathrm{CC}}$ | V |
| $\mathrm{T}_{\mathrm{A}}$ | Operating Temperature Range | -40 | +85 | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{t}_{\mathrm{r}} \mathrm{t}_{\mathrm{f}}$ | Input Rise or Fall Time, SELECT |  | $\mathrm{V}_{\mathrm{CC}}=3.3 \mathrm{~V} \pm 0.3 \mathrm{~V}$ | 0 |
|  |  | $\mathrm{~V}_{\mathrm{CC}}=5.0 \mathrm{~V} \pm 0.5 \mathrm{~V}$ | 0 | 100 |

ANALOG SWITCH DC CHARACTERISTICS

| Symbol | Parameter | Condition | $\mathrm{V}_{\mathrm{cc}}$ (V) | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  |  | Min | Max |  |
| $\mathrm{V}_{\mathrm{IH}}$ | Input Logic High Voltage | $\begin{aligned} & \mathrm{V}_{\text {OUT }}=0.1 \mathrm{~V} \\ & \mathrm{I}_{\text {OUT }} \leq 20 \mu \mathrm{~A} \end{aligned}$ | $\begin{gathered} 1.65 \text { to } 2.2 \\ 2.7 \text { to } 3.6 \\ 4.5 \text { to } 5.5 \end{gathered}$ | $\begin{gathered} \hline \mathrm{V}_{\mathrm{CC}} \times 0.55 \\ \mathrm{~V}_{\mathrm{CC}} \times 0.5 \\ 2.0 \end{gathered}$ | - | V |
| $\mathrm{V}_{\text {IL }}$ | Input Logic Low Voltage | $\begin{gathered} \mathrm{V}_{\text {OUT }}=-\mathrm{V}_{\text {CC }}-0.1 \mathrm{~V} \\ \mathrm{I}_{\text {OUT }} \leq 20 \mu \mathrm{~A} \end{gathered}$ | $\begin{gathered} 1.65 \text { to } 2.2 \\ 2.7 \text { to } 3.6 \\ 4.5 \text { to } 5.5 \end{gathered}$ | - | $\begin{gathered} \mathrm{V}_{\mathrm{CC}} \times 0.2 \\ \mathrm{~V}_{\mathrm{CC}} \times 0.2 \\ 0.8 \end{gathered}$ | V |
| 1 IN | Input Leakage Current | $\mathrm{V}_{\text {IN }}-\mathrm{V}_{\text {CC }}$ or GND | 5.0 | -100 | +100 | nA |
| $\mathrm{V}_{\mathrm{CC}}$ | Power Supply Range | All | - | 1.65 | 5.5 | V |
| $\mathrm{I}_{\mathrm{CC}}$ | Supply Current | $\begin{gathered} \mathrm{V}_{\mathrm{IN}}=\mathrm{V}_{\mathrm{CC}} \text { or } \mathrm{GND} \\ \mathrm{l} \text { OUT }=0 \mu \mathrm{~A} \end{gathered}$ | $\begin{aligned} & 1.8 \\ & 3.3 \\ & 5.0 \end{aligned}$ | - | $\begin{aligned} & 1.0 \\ & 1.0 \\ & 1.0 \end{aligned}$ | $\mu \mathrm{A}$ |
| $\mathrm{V}_{\text {IS }}$ | Analog Signal Range | Key parameter | - | 0 | $\mathrm{V}_{\mathrm{CC}}$ | V |

ANALOG SWITCH CHARACTERISTICS - Digital Section (Voltages Referenced to GND)

| Symbol | Parameter | Condition | $\mathrm{V}_{\mathrm{cc}}(\mathrm{V})$ | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ |  |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  |  | Min | Typ | Max |  |
| $\mathrm{R}_{\mathrm{ON}}$ | ON Resistance (Note 2) | $\begin{gathered} \mathrm{V}_{\mathrm{CC}}=3.0 \mathrm{~V} \\ \mathrm{I}_{\mathrm{COM}}=10 \mathrm{~mA} \\ \mathrm{~V}_{\mathrm{NO}} \text { or } \mathrm{V}_{\mathrm{NC}}=\mathrm{V}_{\mathrm{IH}} \text { or } \mathrm{V}_{\mathrm{IL}} \end{gathered}$ | 3.0 | - |  | 4.5 | $\Omega$ |
|  |  | $\begin{gathered} \mathrm{V}_{\mathrm{CC}}=5.0 \mathrm{~V} \\ \mathrm{I}_{\mathrm{COM}}=10 \mathrm{~mA} \\ \mathrm{~V}_{\mathrm{NO}} \text { or } \mathrm{V}_{\mathrm{NC}}=\mathrm{V}_{\mathrm{IH}} \text { or } \mathrm{V}_{\mathrm{IL}} \end{gathered}$ | 5.0 | - |  | 3.5 |  |
| $\Delta \mathrm{R}_{\text {ON }}$ | ON Resistance Match Between Channels (Note 2 and 3) | $\begin{gathered} \mathrm{V}_{\mathrm{CC}}=3.6 \mathrm{~V} \\ \mathrm{I}_{\mathrm{COM}}=10 \mathrm{~mA} \\ \mathrm{~V}_{\mathrm{NO}} \text { or } \mathrm{V}_{\mathrm{NC}}=\mathrm{V}_{\mathrm{IH}} \text { or } \mathrm{V}_{\mathrm{IL}} \end{gathered}$ | 3.6 | - | 0.1 | 0.4 | $\Omega$ |
|  |  | $\begin{gathered} \mathrm{V}_{\mathrm{CC}}=5.5 \mathrm{~V} \\ \mathrm{I}_{\mathrm{COM}}=10 \mathrm{~mA} \\ \mathrm{~V}_{\mathrm{NO}} \text { or } \mathrm{V}_{\mathrm{NC}}=\mathrm{V}_{\mathrm{IH}} \text { or } \mathrm{V}_{\mathrm{IL}} \end{gathered}$ | 5.5 |  |  |  |  |
| RFLAT[ON] | ON Resistance Flatness (Note 4) | $\begin{aligned} & \mathrm{I}_{\mathrm{COM}}=10 \mathrm{~mA} \\ & \mathrm{~V}_{\mathrm{IS}}=0 \text { to } \mathrm{V}_{\mathrm{CC}} \end{aligned}$ | 3.0 | - |  | 1.5 | $\Omega$ |
|  |  | $\begin{aligned} & \mathrm{I}_{\mathrm{COM}}=10 \mathrm{~mA} \\ & \mathrm{~V}_{\mathrm{IS}}=0 \text { to } \mathrm{V}_{\mathrm{CC}} \end{aligned}$ | 5.5 | - |  | 1.36 |  |
| $\mathrm{I}_{\text {No_[OFF] }}$ INC_[OFF] | $\overline{\mathrm{NO}_{-}, \mathrm{NC}_{-}}$ <br> Off-Leakage Current (Note 5) | $\begin{gathered} \mathrm{V}_{\mathrm{CC}}=3.6 \mathrm{~V} \\ \mathrm{~V}_{\mathrm{COM}}=0.3 \mathrm{~V} \text { or } 3.3 \mathrm{~V} \\ \mathrm{~V}_{\mathrm{NO}} \text { or } \mathrm{V}_{\mathrm{NC}}=0.3 \mathrm{~V} \text { or } 3.3 \mathrm{~V} \end{gathered}$ | 3.6 | -1.0 | 0.01 | +1.0 | nA |
|  |  | $\begin{gathered} \mathrm{V}_{\mathrm{CC}}=5.5 \mathrm{~V} \\ \mathrm{~V}_{\mathrm{COM}}=0 \mathrm{~V} \text { or } 5.0 \mathrm{~V} \\ \mathrm{~V}_{\mathrm{NO}} \text { or } \mathrm{V}_{\mathrm{NC}}=0 \mathrm{~V} \text { or } 5.0 \mathrm{~V} \end{gathered}$ | 5.5 | -1.0 | 0.01 | +1.0 |  |
| $\mathrm{I}_{\text {Com_[ON] }}$ | COM_ <br> On-Leakage Current (Note 5) | $\begin{gathered} \mathrm{V}_{\mathrm{CC}}=3.6 \mathrm{~V} \\ \mathrm{~V}_{\mathrm{COM}}=0.3 \mathrm{~V} \text { or } 3.3 \mathrm{~V} \\ \mathrm{~V}_{\mathrm{NO}} \text { or } \mathrm{V}_{\mathrm{NC}}=0.3 \mathrm{~V} \text { or } 3.3 \mathrm{~V} \end{gathered}$ | 3.6 | -2.0 | 0.01 | +2.0 | nA |
|  |  | $\begin{gathered} \mathrm{V}_{\mathrm{CC}}=5.5 \mathrm{~V} \\ \mathrm{~V}_{\mathrm{COM}}=0 \mathrm{~V} \text { or } 5.0 \mathrm{~V} \\ \mathrm{~V}_{\mathrm{NO}} \text { or } \mathrm{V}_{\mathrm{NC}}=0 \mathrm{~V} \text { or } 5.0 \mathrm{~V} \end{gathered}$ | 5.5 | $-2.0$ | 0.01 | +2.0 |  |

ANALOG SWITCH AC CHARACTERISTICS

| Symbol | Parameter | Condition | $\mathrm{V}_{\mathrm{cc}}(\mathrm{V})$ | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ |  |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  |  | Min | Typ | Max |  |
| ton | Turn-On Time | $\begin{gathered} \mathrm{V}_{\mathrm{NC}_{-}}, \mathrm{V}_{\mathrm{NO}_{-}}=\mathrm{V}_{\mathrm{IH}} \text { or } \mathrm{V}_{\mathrm{IL}} \\ \mathrm{R}_{\mathrm{L}}=300 \Omega, \mathrm{C}_{\mathrm{L}}=35 \mathrm{pF} \\ \mathrm{~V}_{\mathrm{IN}[\mathrm{X}]}=\mathrm{V}_{\mathrm{IH}} \text { or } \mathrm{V}_{\mathrm{IL}} \end{gathered}$ | 1.8 to 5.5 | - | - | 30 | nS |
| toff | Turn-Off Time | $\begin{gathered} \hline \mathrm{V}_{\mathrm{NC}_{-},} \mathrm{V}_{\mathrm{NO}_{-}}=\mathrm{V}_{\mathrm{IH}} \text { or } \mathrm{V}_{\mathrm{IL}} \\ \mathrm{R}_{\mathrm{L}}=300 \Omega, \mathrm{C}_{\mathrm{L}}=35 \mathrm{pF} \\ \mathrm{~V}_{\mathrm{IN}[\mathrm{X}]}=\mathrm{V}_{\mathrm{IH}} \text { or } \mathrm{V}_{\mathrm{IL}} \end{gathered}$ | 1.8 to 5.5 | - | - | 40 | nS |
| $\mathrm{t}_{\text {BBM }}$ | Break-Before-Make Time Delay (Note 5) | $\begin{gathered} \mathrm{V}_{\mathrm{NC}_{-}}, \mathrm{V}_{\mathrm{NO}_{-}}=1.5 \mathrm{~V} \\ \mathrm{R}_{\mathrm{L}}=300 \Omega, \mathrm{C}_{\mathrm{L}}=35 \mathrm{pF} \end{gathered}$ | - | - | 8.0 | - | nS |
| tskew | Skew (Note 5) | $\mathrm{R}_{\mathrm{S}}=39 \Omega, \mathrm{C}_{\mathrm{L}}=50 \mathrm{pF}$ | - | - | 0.15 | 2.0 | nS |

2. R $\mathrm{R}_{\mathrm{ON}}$ characterized for $\mathrm{V}_{\mathrm{CC}}$ range ( 1.65 V to 5.5 V ).
3. $\Delta R_{O N}=R_{O N}(M A X)-R_{O N}(M I N)$.
4. $R_{F L A T I O N]}=R_{O N}(M A X)-R_{O N}(M I N)$, measured over $V_{C C}$ range.
5. Guaranteed by design.

ANALOG SWITCH APPLICATION CHARACTERISTICS

| Symbol | Parameter | Condition | $\mathrm{V}_{\mathrm{cc}}(\mathrm{V})$ | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ |  |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  |  | Min | Typ | Max |  |
| Q | Charge Injection | $\begin{gathered} \mathrm{V}_{\mathrm{IN}}=\mathrm{V}_{\mathrm{CC}} \text { to } \mathrm{GND} \\ \mathrm{R}_{\mathrm{In}}=0 \Omega, \mathrm{C}_{\mathrm{L}}=1.0 \mathrm{nF} \\ \mathrm{Q}=\mathrm{C}_{\mathrm{L}}-\Delta \mathrm{V}_{\text {OUT }} \end{gathered}$ | $\begin{aligned} & 3.0 \\ & 5.0 \end{aligned}$ | $9.0$ |  |  | pC |
| VISO | Off-Isolation | $\begin{gathered} \mathrm{f}=10 \mathrm{MHz} \\ \mathrm{~V}_{\mathrm{NO}_{-},} \mathrm{V}_{\mathrm{NC}_{-}}=1.0 \mathrm{Vp-p} \\ \mathrm{R}_{\mathrm{L}}=50 \Omega, \mathrm{C}_{\mathrm{L}}=5.0 \mathrm{pF} \end{gathered}$ | 1.65 to 5.5 | -50 |  |  | dB |
|  |  | $\begin{gathered} \mathrm{f}=1.0 \mathrm{MHz} \\ \mathrm{~V}_{\text {NO_- }}, \mathrm{V}_{\text {NC_- }}=1.0 \mathrm{Vp-p} \\ \mathrm{R}_{\mathrm{L}}=50 \Omega, \mathrm{C}_{\mathrm{L}}=5.0 \mathrm{pF} \end{gathered}$ |  | -75 |  |  |  |
| VCT | Cross-Talk | $\begin{gathered} \mathrm{f}=10 \mathrm{MHz} \\ \mathrm{~V}_{\mathrm{NO} \mathcal{L},} \mathrm{~V}_{\mathrm{NC}_{-}}=1.0 \mathrm{Vp-p} \\ \mathrm{R}_{\mathrm{L}}=50 \Omega, \mathrm{C}_{\mathrm{L}}=5.0 \mathrm{pF} \end{gathered}$ | 1.65 to 5.5 | -80 |  |  | dB |
|  |  | $\begin{gathered} \mathrm{f}=1.0 \mathrm{MHz} \\ \mathrm{~V}_{\mathrm{NO}}^{-} \end{gathered}, \mathrm{V}_{\mathrm{NC}_{-}}=1.0 \mathrm{Vp-p}, \mathrm{R}_{\mathrm{L}}=50 \Omega, \mathrm{C}_{\mathrm{L}}=5.0 \mathrm{pF} .$ |  | -110 |  |  |  |
| BW | On-Channel -3.0 db Bandwidth | $\begin{gathered} \text { Signal }=0 \mathrm{~dB} \\ \mathrm{R}_{\mathrm{L}}=50 \Omega, C_{\mathrm{L}}=5.0 \mathrm{pF} \end{gathered}$ | 1.8 to 5.0 | 40 |  |  | MHz |
| THD | Total Harmonic Distortion | $\begin{gathered} \mathrm{V}_{\mathrm{COM}}=2.0 \mathrm{Vp-p,} \\ \mathrm{RL}=600 \Omega, \mathrm{~T}_{\mathrm{A}}=25^{\circ} \mathrm{C} \end{gathered}$ | - | 0.02 |  |  | \% |
| $\mathrm{C}_{\text {NO_[OFF] }}$ $\mathrm{C}_{\text {NC_[OFF] }}$ | $\begin{gathered} \text { NO_, NC_- } \\ \text { OFF-Capacitance } \end{gathered}$ | $\mathrm{F}=10 \mathrm{MHz}$ | - | 30 |  |  | pF |
| $\begin{aligned} & \mathrm{C}_{\mathrm{NO} \text { _[ON] }} \\ & \mathrm{C}_{\mathrm{NC} \text { _[ON] }} \end{aligned}$ | NO_, NC_ ON-Capacitance | $\mathrm{F}=10 \mathrm{MHz}$ | - | 110 |  |  | pF |



Figure 2. Low $\mathrm{R}_{\mathrm{DS}(\mathrm{on})} @ \mathrm{~V}_{\mathrm{CC}}=5.0 \mathrm{~V}$


Figure 4. Delta $R_{\mathrm{DS}(o n)} @ \mathrm{~V}_{\mathrm{cc}}=5.0 \mathrm{~V}$


Figure 3. Low $\mathrm{R}_{\mathrm{DS}(\mathrm{on})} @ \mathrm{~V}_{\mathrm{CC}}=3.0 \mathrm{~V}$


Figure 5. Delta $R_{\mathrm{DS}(o n)} @ \mathrm{~V}_{\mathrm{Cc}}=3.0 \mathrm{~V}$


Figure 6. Charge Injection


Figure 7. Total Harmonic Distortion


Figure 8. Frequency Response


Figure 9. Bandwidth and Phase


Figure 10. $\mathrm{t}_{\mathrm{BBM}}$ (Time Break-Before-Make)


Figure 11. $\mathrm{t}_{\mathrm{ON}} / \mathrm{t}_{\mathrm{OFF}}$


Figure 12. $\mathrm{t}_{\mathrm{ON}} / \mathrm{t}_{\mathrm{OFF}}$


Channel switch control/s test socket is normalized. Off isolation is measured across an off channel. On loss is the bandwidth of an On switch. $\mathrm{V}_{\mathrm{ISO}}$, Bandwidth and $\mathrm{V}_{\mathrm{ONL}}$ are independent of the input signal direction.
$V_{\text {ISO }}=$ Off Channel Isolation $=20 \log \left(\frac{V_{\text {OUT }}}{V_{\text {IN }}}\right)$ for $V_{\text {IN }}$ at 100 kHz
$\mathrm{V}_{\mathrm{ONL}}=$ On Channel Loss $=20$ Log $\left(\frac{\mathrm{V}_{\mathrm{OUT}}}{\mathrm{V}_{\mathrm{IN}}}\right)$ for $\mathrm{V}_{\mathrm{IN}}$ at 100 kHz to 50 MHz
Bandwidth (BW) = the frequency 3.0 dB below $\mathrm{V}_{\mathrm{ONL}}$
$\mathrm{V}_{\mathrm{CT}}=$ Use $\mathrm{V}_{\text {ISO }}$ setup and test to all other switch analog input/outputs terminated with $50 \Omega$

Figure 13. Off Channel Isolation/On Channel Loss (BW)/Crosstalk (On Channel to Off Channel)/ $V_{\text {ONL }}$


Figure 14. Charge Injection: (Q)


## 10 PIN FLIP-CHIP

CASE 489AA-01
ISSUE A
DATE 04 MAY 2004

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLING DIMENSION: MILLIMETERS.
3. COPLANARITY APPLIES TO SPHERICAL CROWNS OF SOLDER BALLS.

|  | MILLIMETERS |  |
| :---: | :---: | :---: |
| DIM | MIN | MAX |
| A | --- | 0.650 |
| A1 | 0.210 | 0.270 |
| A2 | 0.280 | 0.380 |
| D | 1.965 BSC |  |
| E | 1.465 BSC |  |
| b | 0.250 | 0.350 |
| e | 0.500 BSC |  |
| D1 | 1.500 BSC |  |
| E1 | 1.000 BSC |  |

GENERIC
MARKING DIAGRAM*

xxxx = Specific Device Code
YY = Year
WW = Work Week
*This information is generic. Please refer to device data sheet for actual part marking. $\mathrm{Pb}-\mathrm{Free}$ indicator, " G " or microdot " r ", may or may not be present.

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| ---: | :--- | :--- | :--- |
| DESCRIPTION: | 10 PIN FLIP-CHIP | PAGE 1 OF 1 |

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Micro10
CASE 846B-03
ISSUE D


SOLDERING FOOTPRINT


Micro10

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982 .
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION "A" DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH, PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION "B" DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 ( 0.010 ) PER SIDE.
5. 846B-01 OBSOLETE. NEW STANDARD 846B-02

| DIM | MILLIMETERS |  | INCHES |  |
| :---: | :---: | :---: | :---: | :---: |
|  | MIN | max | MIN | max |
| A | 2.90 | 3.10 | 0.114 | 0.122 |
| B | 2.90 | 3.10 | 0.114 | 0.122 |
| c | 0.95 | 1.10 | 0.037 | 0.043 |
| D | 0.20 | 0.30 | 0.008 | 0.012 |
| G |  |  | 0.02 |  |
| H | 0.05 | 0.15 | 0.002 | 0.006 |
| J | 0.10 | 0.21 | 0.004 | 0.008 |
| K | 4.75 | 5.05 | 0.187 | 0.199 |
| L | 0.40 | 0.70 | 0.016 | 0.028 |

GENERIC MARKING DIAGRAM*


| xxxx | $=$ Device Code |
| :--- | :--- |
| A | $=$ Assembly Location |
| Y | $=$ Year |
| W | $=$ Work Week |
| - | $=$ Pb-Free Package |

*This information is generic. Please refer to device data sheet for actual part marking. $\mathrm{Pb}-\mathrm{Free}$ indicator, " G " or microdot """, may or may not be present. Some products may not follow the Generic Marking.

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| ---: | :--- | :--- | :--- |
| DESCRIPTION: | Micro10 | PAGE 1 OF 1 |

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